

RJP4301APP

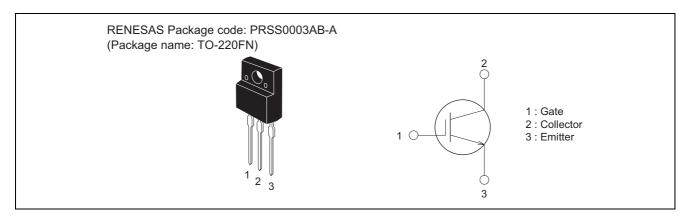
Nch IGBT for Strobe Flash

REJ03G1709-0100 Rev.1.00 Jul 03, 2008

Features

- V_{CES}: 430 V
- TO-220FN package
- High Speed Switching

Outline



Applications

Strobe flash

Maximum Ratings

 $(Tc = 25^{\circ}C)$

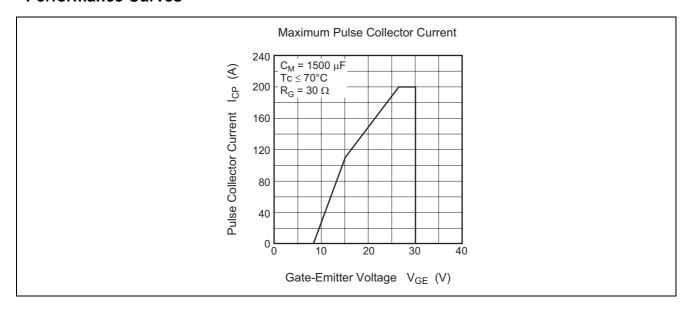
Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V _{CES}	430	V	V _{GE} = 0 V
Gate-emitter voltage	V _{GES}	±33	V	V _{CE} = 0 V, Refer to item 4 under Notes on the Actual Specifications
Collector current (Pulse)	I _{CM}	200	А	$C_M = 1500 \mu F$ (see performance curve)
Maximum power dissipation	Pc	30	W	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value

Electrical Characteristics

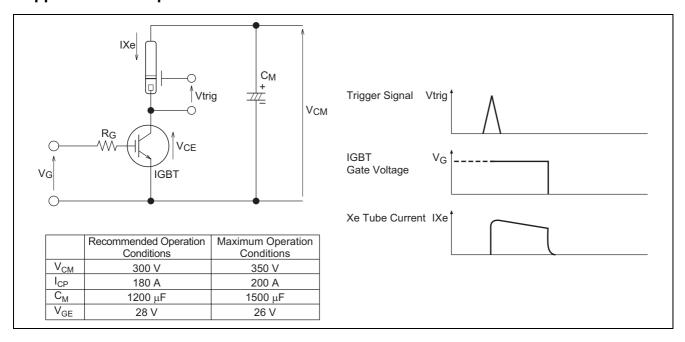
 $(Tj = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	$V_{(BR)CES}$	430	_	_	V	$I_C = 100 \mu\text{A}, V_{GE} = 0 \text{V}$
Collector-emitter leakage current	I _{CES}	_	_	1	μΑ	$V_{CE} = 430 \text{ V}, V_{GE} = 0 \text{ V}$
Gate-emitter leakage current	I _{GES}	_	_	±0.1	μΑ	$V_{GE} = \pm 33 \text{ V}, V_{CE} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{GE(th)}$	3.0	_	5.5	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	V _{CE(sat)}	_	4.0	10	V	I _C = 200 A, V _{GE} = 26 V
Input capacitance	Ciss	_	1150	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	125	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	14	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	0.01	_	μs	V _{DD} = 200 V
Rise time	t _r	_	0.06	_	μs	I _D = 26 A
Turn-off delay time	t _{d(off)}	_	0.15	_	μs	V _{GS} = 300 V
Fall time	t _f	_	0.2	_	μs	$R_G = 25 \Omega$

Performance Curves



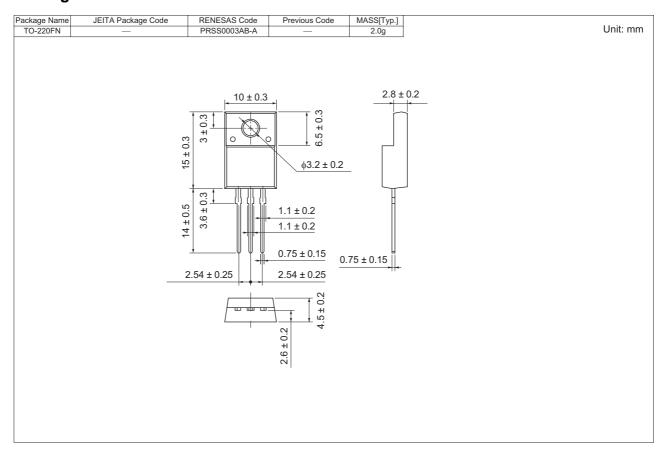
Application Example



Precautions on Usage

- 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And peak reverse gate current during turn-off must become less than 1 A. (In general, when $R_{G(off)} = 30 \Omega$, it is satisfied.)
- 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 3. The operation life should be endured until repeated discharge of 5,000 times under the charge current ($I_{Xe} \le 200 \text{ A}$: full luminescence condition) of main capacitor. Repetition period under full luminescence condition is over 3 seconds
- 4. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours.

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJP4301APP-00-T2	50 pcs	Magazine (Tube)

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